

Features

- Medium-voltage and Standard-voltage Operation
 - 5.0 ($V_{CC} = 4.5V$ to $5.5V$)
 - 2.7 ($V_{CC} = 2.7V$ to $5.5V$)
- User-selectable Internal Organization
 - 1K: 128 x 8 or 64 x 16
 - 2K: 256 x 8 or 128 x 16
 - 4K: 512 x 8 or 256 x 16
- 3-wire Serial Interface
- 2 MHz Clock Rate (5V)
- Self-timed Write Cycle (10 ms max)
- High Reliability
 - Endurance: 1 Million Write Cycles
 - Data Retention: 100 Years
- 8-lead PDIP and 8-lead JEDEC SOIC Packages

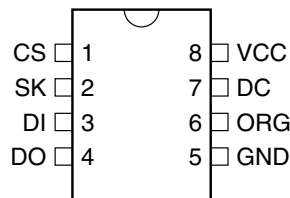
Description

The AT93C46/56/66 provides 1024/2048/4096 bits of serial electrically erasable programmable read only memory (EEPROM) organized as 64/128/256 words of 16 bits each, when the ORG pin is connected to VCC and 128/256/512 words of 8 bits each when it is tied to ground. The device is optimized for use in many automotive applications where low power and low voltage operations are essential. The AT93C46/56/66 is available in space-saving 8-lead PDIP and 8-lead JEDEC SOIC packages.

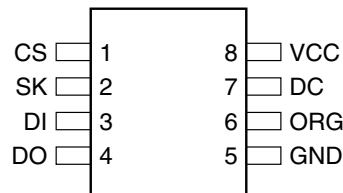
Pin Configurations

Pin Name	Function
CS	Chip Select
SK	Serial Data Clock
DI	Serial Data Input
DO	Serial Data Output
GND	Ground
VCC	Power Supply
ORG	Internal Organization
DC	Don't Connect

8-lead PDIP



8-lead SOIC



3-wire Serial Automotive EEPROMs

1K (128 x 8 or 64 x 16)

2K (256 x 8 or 128 x 16)

4K (512 x 8 or 256 x 16)

AT93C46

AT93C56

AT93C66

Description (Continued)

The AT93C46/56/66 is enabled through the Chip Select pin (CS), and accessed via a 3-wire serial interface consisting of Data Input (DI), Data Output (DO), and Shift Clock (SK). Upon receiving a READ instruction at DI, the address is decoded and the data is clocked out serially on the data output pin DO. The WRITE cycle is completely self-timed and no separate ERASE cycle is required before WRITE. The WRITE cycle is only enabled when the part is in the ERASE/WRITE ENABLE state. When CS is brought “high” following the initiation of a WRITE cycle, the DO pin outputs the READY/BUSY status of the part.

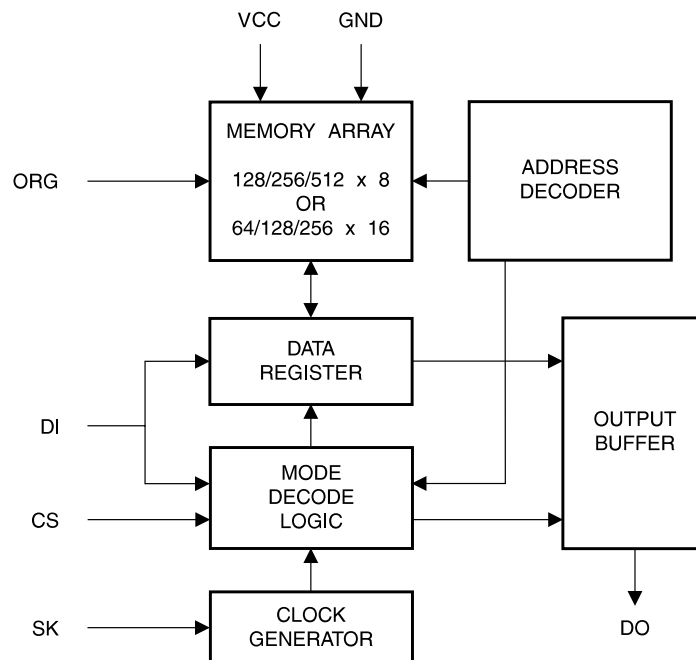
The AT93C46/56/66 is available in 4.5V to 5.5V and 2.7V to 5.5V versions.

Absolute Maximum Ratings*

Operating Temperature	-55°C to +125°C
Storage Temperature	-65°C to +150°C
Voltage on Any Pin with Respect to Ground	-1.0V to +7.0V
Maximum Operating Voltage	6.25V
DC Output Current.....	5.0 mA

***NOTICE:** Stresses beyond those listed under “Absolute Maximum Ratings” may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability

Block Diagram



- Notes:
1. When the ORG pin is connected to VCC, the x 16 organization is selected. When it is connected to ground, the x 8 organization is selected. If the ORG pin is left unconnected and the application does not load the input beyond the capability of the internal 1 Meg ohm pullup, then the x 16 organization is selected.
 2. For the AT93C46, if x 16 organization is the mode of choice and Pin 6 (ORG) is left unconnected, Atmel recommends using the AT93C46A device. For more details, see the AT93C46A datasheet.

Pin Capacitance⁽¹⁾

Applicable over recommended operating range from $T_A = 25^\circ\text{C}$, $f = 1.0\text{ MHz}$, $V_{CC} = +5.0\text{V}$ (unless otherwise noted).

Symbol	Test Conditions	Max	Units	Conditions
C_{OUT}	Output Capacitance (DO)	5	pF	$V_{OUT} = 0\text{V}$
C_{IN}	Input Capacitance (CS, SK, DI)	5	pF	$V_{IN} = 0\text{V}$

Note: 1. This parameter is characterized and is not 100% tested.

DC Characteristics

Applicable over recommended operating range from: $T_A = -40^\circ\text{C}$ to $+125^\circ\text{C}$, $V_{CC} = +2.7\text{V}$ to $+5.5\text{V}$ (unless otherwise noted).

Symbol	Parameter	Test Condition	Min	Typ	Max	Unit
V_{CC1}	Supply Voltage		2.7		5.5	V
V_{CC2}	Supply Voltage		4.5		5.5	V
I_{CC}	Supply Current	$V_{CC} = 5.0\text{V}$	READ at 1.0 MHz	0.5	2.0	mA
			WRITE at 1.0 MHz	0.5	2.0	mA
I_{SB1}	Standby Current	$V_{CC} = 2.7\text{V}$	CS = 0V	6.0	10.0	μA
I_{SB2}	Standby Current	$V_{CC} = 5.0\text{V}$	CS = 0V	17	30	μA
I_{IL}	Input Leakage	$V_{IN} = 0\text{V}$ to V_{CC}		0.1	1.0	μA
I_{OL}	Output Leakage	$V_{IN} = 0\text{V}$ to V_{CC}		0.1	1.0	μA
$V_{IL1}^{(1)}$ $V_{IH1}^{(1)}$	Input Low Voltage Input High Voltage	$2.7\text{V} \leq V_{CC} \leq 5.5\text{V}$	-0.6 $V_{CC} \times 0.7$		$V_{CC} \times 0.3$ $V_{CC} + 1$	V
V_{OL1} V_{OH1}	Output Low Voltage Output High Voltage	$4.5\text{V} \leq V_{CC} \leq 5.5\text{V}$	$I_{OL} = 2.1\text{ mA}$		0.4	V
			$I_{OH} = -0.4\text{ mA}$	2.4		V
V_{OL2} V_{OH2}	Output Low Voltage Output High Voltage	$1.8\text{V} \leq V_{CC} \leq 2.7\text{V}$	$I_{OL} = 0.15\text{ mA}$		0.2	V
			$I_{OH} = -100\ \mu\text{A}$	$V_{CC} - 0.2$		V

Note: 1. V_{IL} min and V_{IH} max are reference only and are not tested.

AC Characteristics

Applicable over recommended operating range from $T_A = -40^\circ\text{C}$ to $+125^\circ\text{C}$, $V_{CC} = \text{As Specified}$,
 $CL = 1$ TTL Gate and 100 pF (unless otherwise noted).

Symbol	Parameter	Test Condition	Min	Typ	Max	Units
f_{SK}	SK Clock Frequency	$4.5V \leq V_{CC} \leq 5.5V$ $2.7V \leq V_{CC} \leq 5.5V$	0 0		2 1	MHz
t_{SKH}	SK High Time	$4.5V \leq V_{CC} \leq 5.5V$ $2.7V \leq V_{CC} \leq 5.5V$	250 250			ns
t_{SKL}	SK Low Time	$4.5V \leq V_{CC} \leq 5.5V$ $2.7V \leq V_{CC} \leq 5.5V$	250 250			ns
t_{CS}	Minimum CS Low Time	$4.5V \leq V_{CC} \leq 5.5V$ $2.7V \leq V_{CC} \leq 5.5V$	250 250			ns
t_{CSS}	CS Setup Time	Relative to SK $4.5V \leq V_{CC} \leq 5.5V$ $2.7V \leq V_{CC} \leq 5.5V$	50 50			ns
t_{DIS}	DI Setup Time	Relative to SK $4.5V \leq V_{CC} \leq 5.5V$ $2.7V \leq V_{CC} \leq 5.5V$	100 100			ns
t_{CSH}	CS Hold Time	Relative to SK	0			ns
t_{DIH}	DI Hold Time	Relative to SK $4.5V \leq V_{CC} \leq 5.5V$ $2.7V \leq V_{CC} \leq 5.5V$	100 100			ns
t_{PD1}	Output Delay to '1'	AC Test $4.5V \leq V_{CC} \leq 5.5V$ $2.7V \leq V_{CC} \leq 5.5V$			250 500	ns
t_{PD0}	Output Delay to '0'	AC Test $4.5V \leq V_{CC} \leq 5.5V$ $2.7V \leq V_{CC} \leq 5.5V$			250 500	ns
t_{SV}	CS to Status Valid	AC Test $4.5V \leq V_{CC} \leq 5.5V$ $2.7V \leq V_{CC} \leq 5.5V$			250 250	ns
t_{DF}	CS to DO in High Impedance	AC Test CS = V_{IL} $4.5V \leq V_{CC} \leq 5.5V$ $2.7V \leq V_{CC} \leq 5.5V$			100 100	ns
t_{WP}	Write Cycle Time				10	ms
		$2.7V \leq V_{CC} \leq 5.5V$		3		ms
Endurance ⁽¹⁾	5.0V, 25°C, Page Mode		1M			Write Cycles

Note: 1. This parameter is characterized and is not 100% tested.

Instruction Set for the AT93C46

Instruction	SB	Op Code	Address		Data		Comments
			x 8	x 16	x 8	x 16	
READ	1	10	A ₆ - A ₀	A ₅ - A ₀			Reads data stored in memory, at specified address.
EWEN	1	00	11XXXXXX	11XXXX			Write enable must precede all programming modes.
ERASE	1	11	A ₆ - A ₀	A ₅ - A ₀			Erase memory location A _n - A ₀ .
WRITE	1	01	A ₆ - A ₀	A ₅ - A ₀	D ₇ - D ₀	D ₁₅ - D ₀	Writes memory location A _n - A ₀ .
ERAL	1	00	10XXXXXX	10XXXX			Erases all memory locations. Valid only at V _{CC} = 4.5V to 5.5V.
WRAL	1	00	01XXXXXX	01XXXX	D ₇ - D ₀	D ₁₅ - D ₀	Writes all memory locations. Valid only at V _{CC} = 4.5V to 5.5V.
EWDS	1	00	00XXXXXX	00XXXX			Disables all programming instructions.

Note: The X's in the address field represent don't care values and must be clocked.

Functional Description

The AT93C46/56/66 is accessed via a simple and versatile 3-wire serial communication interface. Device operation is controlled by seven instructions issued by the host processor. **A valid instruction starts with a rising edge of CS** and consists of a Start Bit (logic “1”) followed by the appropriate Op Code and the desired memory Address location.

READ (READ): The Read (READ) instruction contains the Address code for the memory location to be read. After the instruction and address are decoded, data from the selected memory location is available at the serial output pin DO. Output data changes are synchronized with the rising edges of serial clock SK. It should be noted that a dummy bit (logic “0”) precedes the 8- or 16-bit data output string.

ERASE/WRITE (EWEN): To assure data integrity, the part automatically goes into the Erase/Write Disable (EWDS) state when power is first applied. An Erase/Write Enable (EWEN) instruction must be executed first before any programming instructions can be carried out. Please note that once in the Erase/Write Enable state, programming remains enabled until an Erase/Write Disable (EWDS) instruction is executed or V_{CC} power is removed from the part.

ERASE (ERASE): The Erase (ERASE) instruction programs all bits in the specified memory location to the logical “1” state. The self-timed erase cycle starts once the ERASE instruction and address are decoded. The DO pin outputs the READY/BUSY status of the part if CS is brought high after being kept low for a minimum of 250 ns (t_{CS}). A logic “1” at pin DO indicates that the selected memory location has been erased, and the part is ready for another instruction.

WRITE (WRITE): The Write (WRITE) instruction contains the 8 or 16 bits of data to be written into the specified memory location. The self-timed programming cycle, t_{WP} , starts after the last bit of data is received at serial data input pin DI. The DO pin outputs the READY/BUSY status of the part if CS is brought high after being kept low for a minimum of 250 ns (t_{CS}). A logic “0” at DO indicates that programming is still in progress. A logic “1” indicates that the memory location at the specified address has been written with the data pattern contained in the instruction and the part is ready for further instructions. **A READY/BUSY status cannot be obtained if the CS is brought high after the end of the self-timed programming cycle, t_{WP} .**

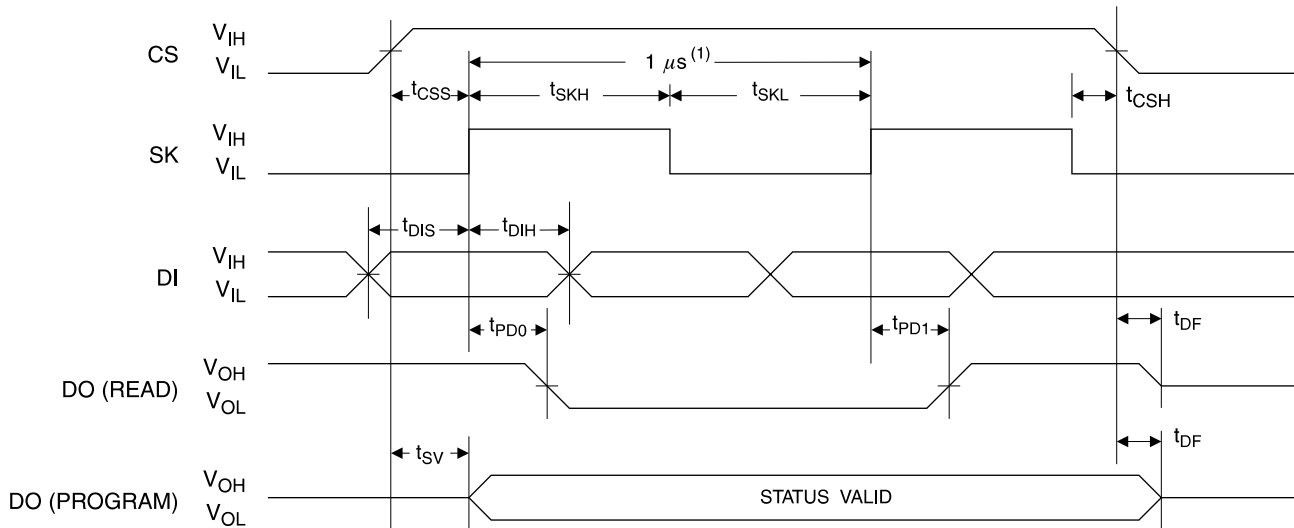
ERASE ALL (ERAL): The Erase All (ERAL) instruction programs every bit in the memory array to the logic “1” state and is primarily used for testing purposes. The DO pin outputs the READY/BUSY status of the part if CS is brought high after being kept low for a minimum of 250 ns (t_{CS}). The ERAL instruction is valid only at $V_{CC} = 5.0V \pm 10\%$.

WRITE ALL (WRAL): The Write All (WRAL) instruction programs all memory locations with the data patterns specified in the instruction. The DO pin outputs the READY/BUSY status of the part if CS is brought high after being kept low for a minimum of 250 ns (t_{CS}). The WRAL instruction is valid only at $V_{CC} = 5.0V \pm 10\%$.

ERASE/WRITE DISABLE (EWDS): To protect against accidental data disturb, the Erase/Write Disable (EWDS) instruction disables all programming modes and should be executed after all programming operations. The operation of the READ instruction is independent of both the EWEN and EWDS instructions and can be executed at any time.

Timing Diagrams

Synchronous Data Timing



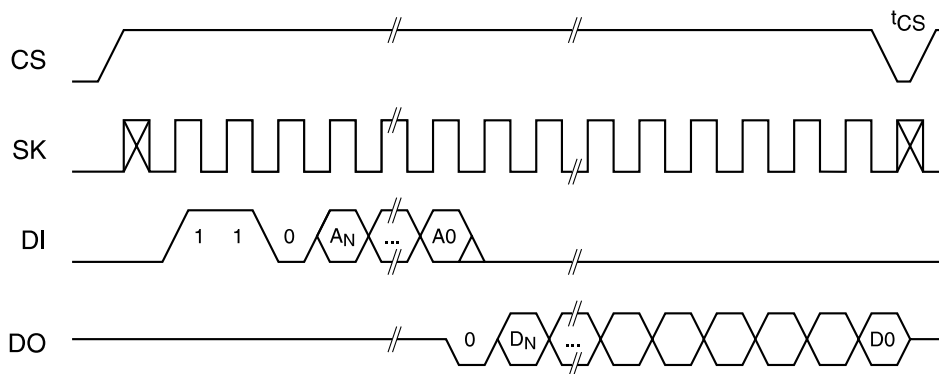
Note: 1. This is the minimum SK period.

Organization Key for Timing Diagrams

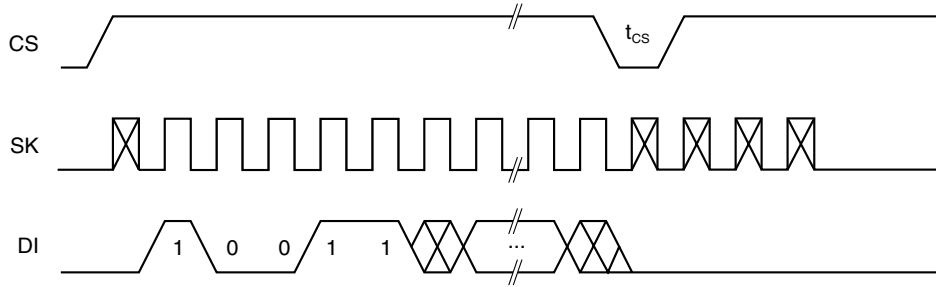
I/O	AT93C46 (1K)		AT93C56 (2K)		AT93C66 (4K)	
	x 8	x 16	x 8	x 16	x 8	x 16
A _N	A ₆	A ₅	A ₈ ⁽¹⁾	A ₇ ⁽²⁾	A ₈	A ₇
D _N	D ₇	D ₁₅	D ₇	D ₁₅	D ₇	D ₁₅

Notes: 1. A₈ is a DON'T CARE value, but the extra clock is required.
2. A₇ is a DON'T CARE value, but the extra clock is required.

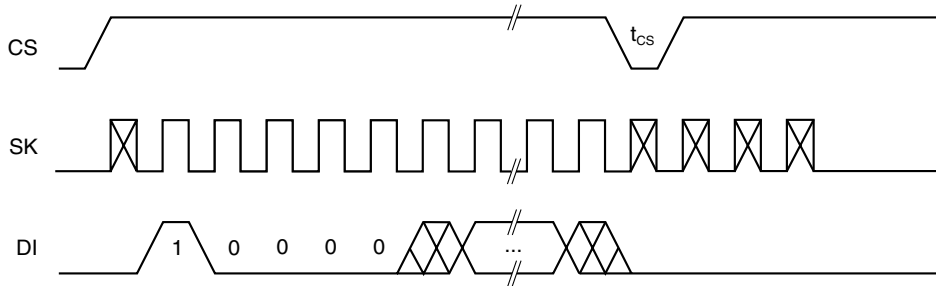
READ Timing



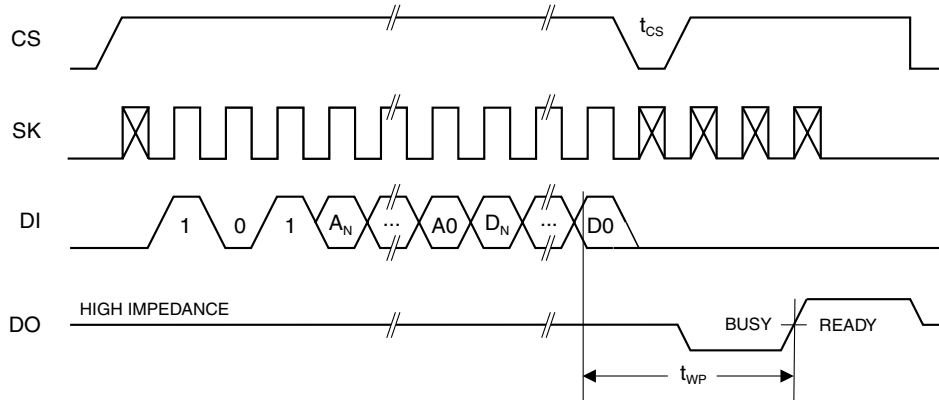
EWEN Timing



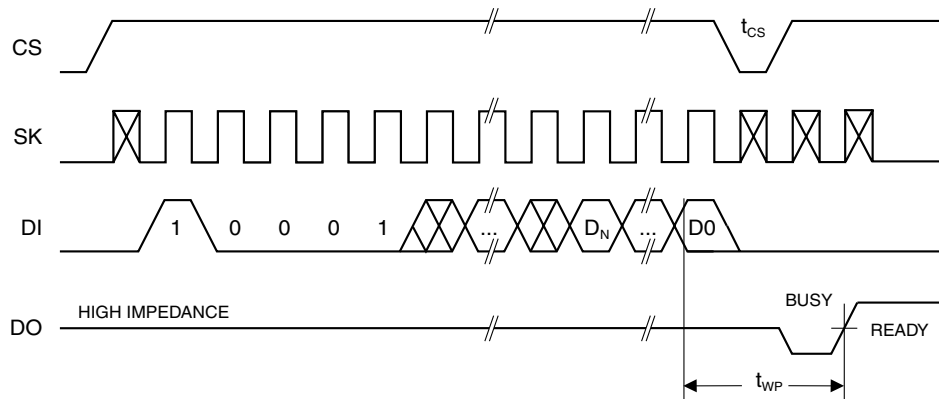
EWDS Timing



WRITE Timing

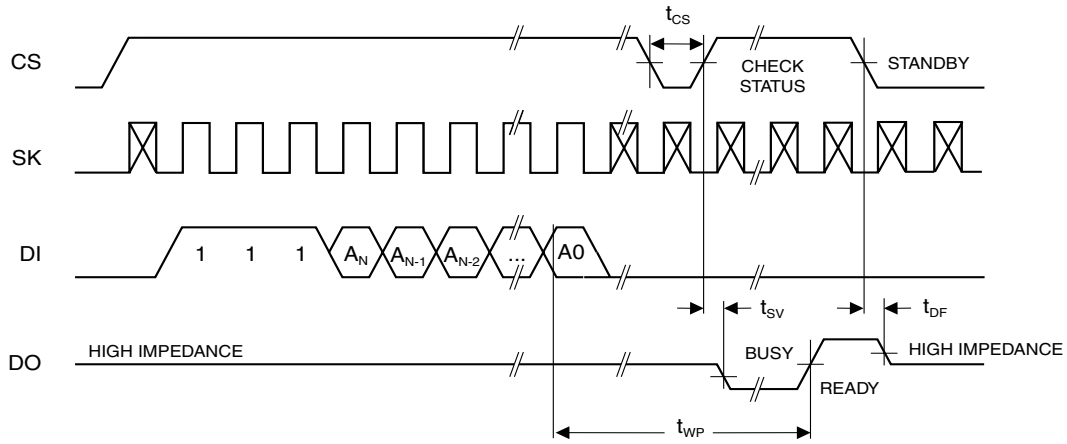


WRAL Timing⁽¹⁾

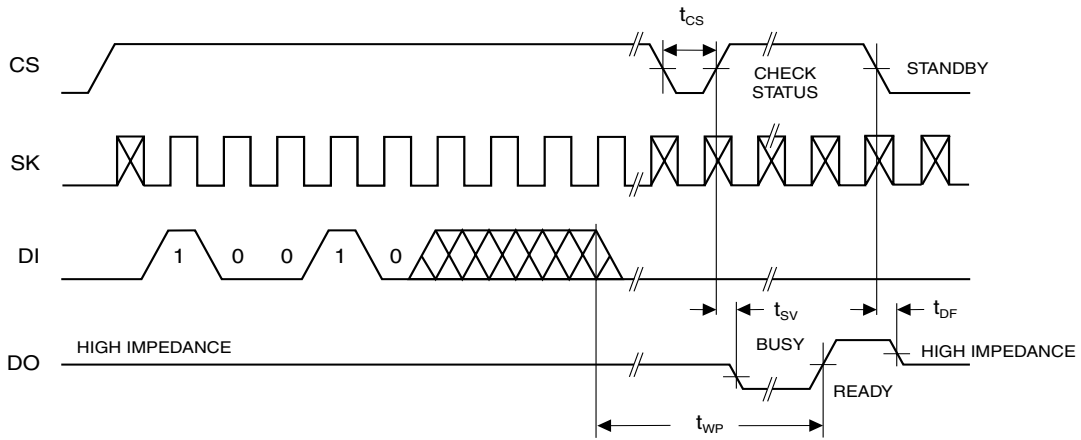


Note: 1. Valid only at $V_{CC} = 4.5V$ to $5.5V$.

ERASE Timing



ERAL Timing⁽¹⁾



Note: 1. Valid only at $V_{CC} = 4.5V$ to $5.5V$.



AT93C46 Ordering Information

t_{WP} (max) (ms)	I_{CC} (max) (μ A)	I_{SB} (max) (μ A)	f_{MAX} (kHz)	Ordering Code	Package	Operation Range
10	2000	30.0	2000	AT93C46-10PA-5.0C AT93C46-10SA-5.0C	8P3 8S1	Automotive (-40°C to 125°C)
10	800	10.0	1000	AT93C46-10PA-2.7C AT93C46-10SA-2.7C	8P3 8S1	Automotive (-40°C to 125°C)

Package Type	
8P3	8-lead, 0.300" Wide, Plastic Dual Inline Package (PDIP)
8S1	8-lead, 0.150" Wide, Plastic Gull Wing Small Outline (JEDEC SOIC)
Options	
-5.0	Standard Operation (4.5V to 5.5V)
-2.7	Low Voltage (2.7V to 5.5V)

AT93C56 Ordering Information

t_{WP} (max) (ms)	I_{CC} (max) (μA)	I_{SB} (max) (μA)	f_{MAX} (kHz)	Ordering Code	Package	Operation Range
10	2000	30.0	2000	AT93C56-10PA-5.0C AT93C56-10SA-5.0C	8P3 8S1	Automotive (-40°C to 125°C)
10	800	10.0	1000	AT93C56-10PA-2.7C AT93C56-10SA-2.7C	8P3 8S1	Automotive (-40°C to 125°C)

Package Type	
8P3	8-lead, 0.300" Wide, Plastic Dual Inline Package (PDIP)
8S1	8-lead, 0.150" Wide, Plastic Gull Wing Small Outline (JEDEC SOIC)
Options	
-5.0	Standard Operation (4.5V to 5.5V)
-2.7	Low Voltage (2.7V to 5.5V)



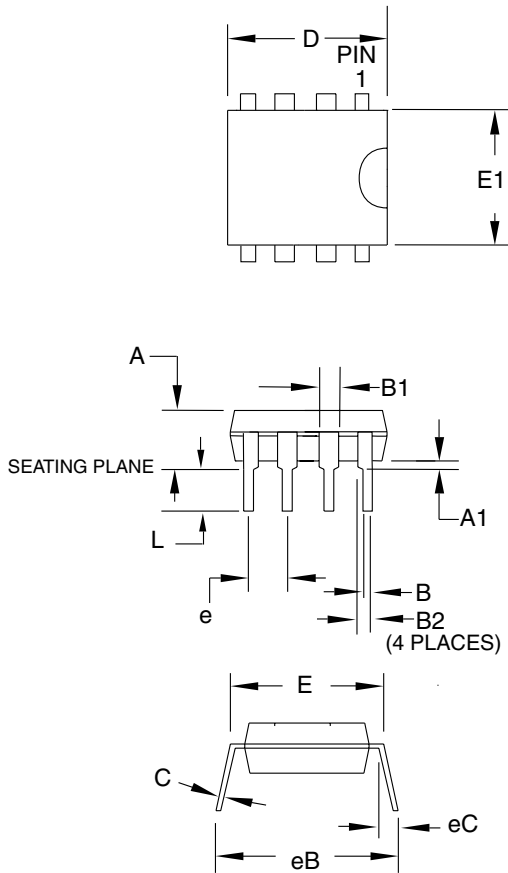
AT93C66 Ordering Information

t_{WP} (max) (ms)	I_{CC} (max) (μA)	I_{SB} (max) (μA)	f_{MAX} (kHz)	Ordering Code	Package	Operation Range
10	2000	30.0	2000	AT93C66-10PA-5.0C AT93C66-10SA-5.0C	8P3 8S1	Automotive (-40°C to 125°C)
10	800	10.0	1000	AT93C66-10PA-2.7C AT93C66-10SA-2.7C	8P3 8S1	Automotive (-40°C to 125°C)

Package Type	
8P3	8-lead, 0.300" Wide, Plastic Dual Inline Package (PDIP)
8S1	8-lead, 0.150" Wide, Plastic Gull Wing Small Outline (JEDEC SOIC)
Options	
-5.0	Standard Operation (4.5V to 5.5V)
-2.7	Low Voltage (2.7V to 5.5V)

Packaging Information

8P3 – PDIP



COMMON DIMENSIONS
(Unit of Measure = mm)

SYMBOL	MIN	NOM	MAX	NOTE
A	–	–	4.318	
A1	0.381	–	–	
D	9.144	–	9.652	Note 2
E	7.620	–	8.255	
E1	6.096	–	6.604	Note 2
B	0.406	–	0.508	
B1	1.397	–	1.651	
B2	0.762	–	1.143	
L	3.175	–	3.429	
C	0.203	–	0.356	
eB	–	–	10.922	
eC	0.000	–	1.524	
e	2.540 TYP			

- Notes:
1. This package conforms to JEDEC reference MS-001 BA.
 2. Dimensions D and E1 do not include mold Flash or Protrusion. Mold Flash or Protrusion shall not exceed 0.25 mm (0.010").

09/28/01



2325 Orchard Parkway
San Jose, CA 95131

TITLE

8P3, 8-lead (0.300"/7.62 mm Wide) Plastic Dual
Inline Package (PDIP)

DRAWING NO.

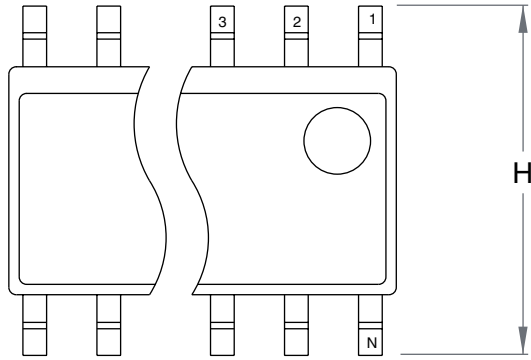
8P3

REV.

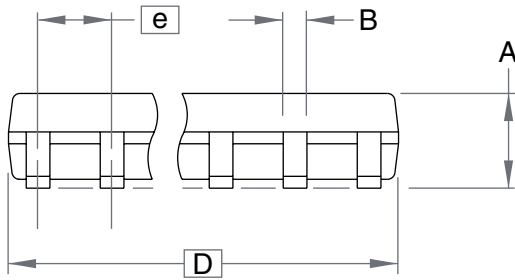
B



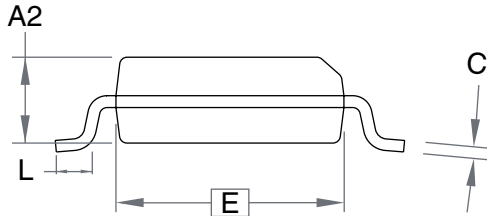
8S2 – JEDEC SOIC



Top View



Side View



End View

COMMON DIMENSIONS
(Unit of Measure = mm)

SYMBOL	MIN	NOM	MAX	NOTE
A	–	–	1.75	
B	–	–	0.51	
C	–	–	0.25	
D	–	–	5.00	
E	–	–	4.00	
e	1.27 BSC			
H	–	–	6.20	
L	–	–	1.27	

Note: This drawing is for general information only. Refer to JEDEC Drawing MS-012 for proper dimensions, tolerances, datums, etc.

10/10/01



2325 Orchard Parkway
San Jose, CA 95131

TITLE
8S1, 8-lead (0.150" Wide Body), Plastic Gull Wing
Small Outline (JEDEC SOIC)

DRAWING NO.
8S1

REV.
A



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